



AiP74AHC/AHCT1G125

Single Buffer/Line Driver; 3-state

Product Specification

Specification Revision History:

Version	Date	Description
2018-08-A1	2018-08	New
2023-04-B1	2023-04	Update the template



Contents

1、 General Description.....	1
2、 Block Diagram And Pin Description	2
2.1、 Block Diagram	2
2.2、 Pin Configurations.....	2
2.3、 Pin Description	2
3、 Electrical Parameter	3
3.1、 Absolute Maximum Ratings.....	3
3.3、 Electrical Characteristics	4
3.3.1、 DC Characteristics 1	4
3.3.2、 DC Characteristics 2.....	5
3.3.3、 DC Characteristics 3	6
3.3.4、 AC Characteristics 1	7
3.3.5、 AC Characteristics 2.....	8
3.3.6、 AC Characteristics 3	9
4、 Testing Circuit	11
5、 Package Information	13
5.1、 SOT23-5.....	13
5.2、 SOT353	14
6、 Statements And Notes	15
6.1、 The name and content of Hazardous substances or Elements in the product.....	15
6.2、 Notes	15



1、General Description

AiP74AHC1G125 and AiP74AHCT1G125 are high-speed Si-gate CMOS devices. They provide one non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (\overline{OE}). A HIGH at \overline{OE} causes the output to assume a high-impedance OFF-state.

The AHC device has CMOS input switching levels and supply voltage range 2V to 5.5V.

The AHCT device has TTL input switching levels and supply voltage range 4.5V to 5.5V.

Features:

- Symmetrical output impedance
- Low power dissipation
- Balanced propagation delays
- Specified from -40°C to +125°C
- Packaging information: SOT23-5/SOT353

Ordering Information:

Reel packing specifications:

Part number	Packaging form	Marking code	Reel quantity	Boxed reel quantity	Notes
AiP74AHC1G125GB235.TR	SOT23-5	DFXX	3000PCS/reel	30000PCS/box	Dimensions of plastic enclosure: 2.9mm×1.6mm Pin spacing: 0.95mm
AiP74AHC1G125GC353.TR	SOT353	DFXX	3000PCS/reel	30000PCS/box	Dimensions of plastic enclosure: 2.1mm×1.3mm Pin spacing: 0.65mm
AiP74AHCT1G125GB235.TR	SOT23-5	DGXX	3000PCS/reel	30000PCS/box	Dimensions of plastic enclosure: 2.9mm×1.6mm Pin spacing: 0.95mm
AiP74AHCT1G125GC353.TR	SOT353	DGXX	3000PCS/reel	30000PCS/box	Dimensions of plastic enclosure: 2.1mm×1.3mm Pin spacing: 0.65mm

Note 1: "XX" refers to variable content, meaning year and package batch serial number.

Note 2: If the physical information is inconsistent with the ordering information, please refer to the actual product.



2、Block Diagram And Pin Description

2.1、Block Diagram

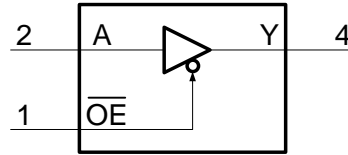


Figure 1. Logic symbol

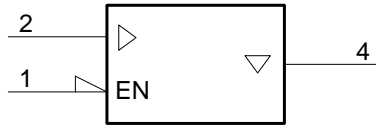


Figure 2. IEC logic symbol

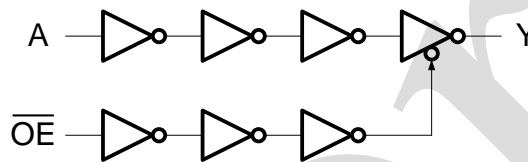


Figure 3. Logic diagram

2.2、Pin Configurations

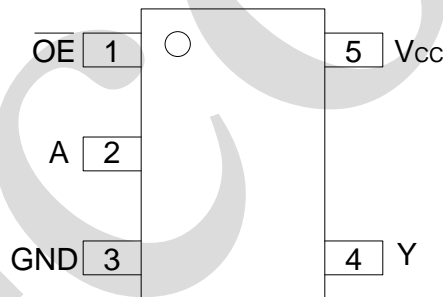


Figure 4. Pin Configurations

2.3、Pin Description

Pin No.	Pin Name	Description
1	$\overline{\text{OE}}$	output enable input
2	A	data input
3	GND	ground (0V)
4	Y	data output
5	V _{CC}	supply voltage



2.4、Function Table

Inputs		Output
$\overline{\text{OE}}$	A	Y
L	L	L
L	H	H
H	X	Z

Note: H=HIGH voltage level; L=LOW voltage level; X=don't care; Z=high-impedance OFF-state.

3、Electrical Parameter

3.1、Absolute Maximum Ratings

($T_{\text{amb}}=25^{\circ}\text{C}$, All voltage referenced to GND, unless otherwise specified)

Characteristic	Symbol	Conditions	Min.	Max.	Unit
supply voltage	V_{CC}	-	-0.5	+7.0	V
input voltage	V_{I}	-	-0.5	+7.0	V
input clamping current	I_{IK}	$V_{\text{I}} < -0.5\text{V}$	-20	-	mA
output clamping current	I_{OK}	$V_{\text{O}} < -0.5\text{V}$ or $V_{\text{O}} > V_{\text{CC}} + 0.5\text{V}$	-	± 20	mA
output current	I_{O}	$0.5\text{V} < V_{\text{O}} < V_{\text{CC}} + 0.5\text{V}$	-	± 25	mA
supply current	I_{CC}	-	-	75	mA
ground current	I_{GND}	-	-75	-	mA
storage temperature	T_{stg}	-	-65	+150	$^{\circ}\text{C}$
total power dissipation	P_{tot}	-	-	250	mW
soldering temperature	T_{L}	10s	260		$^{\circ}\text{C}$

3.2、Recommended Operating Conditions

(Voltages are referenced to GND (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
AiP74AHC1G125						
supply voltage	V_{CC}	-	2.0	5.0	5.5	V
input voltage	V_{I}	-	0	-	5.5	V
output voltage	V_{O}	-	0	-	V_{CC}	V
ambient temperature	T_{amb}	-	-40	-	+125	$^{\circ}\text{C}$
input transition rise and fall rate	$\Delta t/\Delta V$	$V_{\text{CC}}=3.3\text{V}\pm 0.3\text{V}$	-	-	100	ns/V
		$V_{\text{CC}}=5.0\text{V}\pm 0.5\text{V}$	-	-	20	ns/V
AiP74AHCT1G125						
supply voltage	V_{CC}	-	4.5	5.0	5.5	V
input voltage	V_{I}	-	0	-	5.5	V
output voltage	V_{O}	-	0	-	V_{CC}	V
ambient temperature	T_{amb}	-	-40	-	+125	$^{\circ}\text{C}$
input transition rise and fall rate	$\Delta t/\Delta V$	$V_{\text{CC}}=3.3\text{V}\pm 0.3\text{V}$	-	-	-	ns/V
		$V_{\text{CC}}=5.0\text{V}\pm 0.5\text{V}$	-	-	20	ns/V



3.3、Electrical Characteristics

3.3.1、DC Characteristics 1

($T_{amb}=25^{\circ}\text{C}$, voltages are referenced to GND (ground=0V), unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
AiP74AHC1G125							
HIGH-level input voltage	V_{IH}	$V_{CC}=2.0\text{V}$	1.5	-	-	V	
		$V_{CC}=3.0\text{V}$	2.1	-	-	V	
		$V_{CC}=5.5\text{V}$	3.85	-	-	V	
LOW-level input voltage	V_{IL}	$V_{CC}=2.0\text{V}$	-	-	0.5	V	
		$V_{CC}=3.0\text{V}$	-	-	0.9	V	
		$V_{CC}=5.5\text{V}$	-	-	1.65	V	
HIGH-level output voltage	V_{OH}	$V_I=V_{IH}$ or V_{IL}	$I_O=-50\mu\text{A}; V_{CC}=2.0\text{V}$	1.9	2.0	-	V
			$I_O=-50\mu\text{A}; V_{CC}=3.0\text{V}$	2.9	3.0	-	V
			$I_O=-50\mu\text{A}; V_{CC}=4.5\text{V}$	4.4	4.5	-	V
			$I_O=-4\text{mA}; V_{CC}=3.0\text{V}$	2.58	-	-	V
			$I_O=-8\text{mA}; V_{CC}=4.5\text{V}$	3.94	-	-	V
LOW-level output voltage	V_{OL}	$V_I=V_{IH}$ or V_{IL}	$I_O=50\mu\text{A}; V_{CC}=2.0\text{V}$	-	0	0.1	V
			$I_O=50\mu\text{A}; V_{CC}=3.0\text{V}$	-	0	0.1	V
			$I_O=50\mu\text{A}; V_{CC}=4.5\text{V}$	-	0	0.1	V
			$I_O=4\text{mA}; V_{CC}=3.0\text{V}$	-	-	0.36	V
			$I_O=8\text{mA}; V_{CC}=4.5\text{V}$	-	-	0.36	V
OFF-state output current	I_{OZ}	$V_I=V_{CC}$ or GND; $V_{CC}=5.5\text{V}$	-	-	1.0	μA	
input leakage current	I_I	$V_I=5.5\text{V}$ or GND; $V_{CC}=0\text{V}$ to 5.5V	-	-	1.0	μA	
supply current	I_{CC}	$V_I=V_{CC}$ or GND; $I_O=0\text{A}$; $V_{CC}=5.5\text{V}$	-	-	1.0	μA	
Input capacitance	C_I	-	-	1.5	10	pF	
AiP74AHCT1G125							
HIGH-level input voltage	V_{IH}	$V_{CC}=4.5\text{V}$ to 5.5V	2.0	-	-	V	
LOW-level input voltage	V_{IL}	$V_{CC}=4.5\text{V}$ to 5.5V	-	-	0.8	V	
HIGH-level output voltage	V_{OH}	$V_I=V_{IH}$ or V_{IL}	$I_O=-50\mu\text{A}; V_{CC}=4.5\text{V}$	4.4	4.5	-	V
			$I_O=-8\text{mA}; V_{CC}=4.5\text{V}$	3.94	-	-	V
LOW-level output voltage	V_{OL}	$V_I=V_{IH}$ or V_{IL}	$I_O=50\mu\text{A}; V_{CC}=4.5\text{V}$	-	0	0.1	V
			$I_O=8\text{mA}; V_{CC}=4.5\text{V}$	-	-	0.36	V
OFF-state output current	I_{OZ}	$V_I=V_{CC}$ or GND; $V_{CC}=5.5\text{V}$	-	-	1.0	μA	
input leakage current	I_I	$V_I=5.5\text{V}$ or GND; $V_{CC}=0\text{V}$ to 5.5V	-	-	1.0	μA	
supply current	I_{CC}	$V_I=V_{CC}$ or GND; $I_O=0\text{A}$; $V_{CC}=5.5\text{V}$	-	-	1.0	μA	



additional supply current	ΔI_{CC}	per input pin; $V_I=3.4V$; other inputs at V_{CC} or GND; $I_O=0A$; $V_{CC}=5.5V$	-	-	1.35	mA
input capacitance	C_I	-	-	1.5	10	pF

3.3.2、DC Characteristics 2

($T_{amb}=-40^{\circ}C$ to $+85^{\circ}C$, voltages are referenced to GND (ground=0V), unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
AiP74AHC1G125							
HIGH-level input voltage	V_{IH}	$V_{CC}=2.0V$	1.5	-	-	V	
		$V_{CC}=3.0V$	2.1	-	-	V	
		$V_{CC}=5.5V$	3.85	-	-	V	
LOW-level input voltage	V_{IL}	$V_{CC}=2.0V$	-	-	0.5	V	
		$V_{CC}=3.0V$	-	-	0.9	V	
		$V_{CC}=5.5V$	-	-	1.65	V	
HIGH-level output voltage	V_{OH}	$V_I=V_{IH}$ or V_{IL}	$I_O=-50\mu A$; $V_{CC}=2.0V$	1.9	-	-	V
			$I_O=-50\mu A$; $V_{CC}=3.0V$	2.9	-	-	V
			$I_O=-50\mu A$; $V_{CC}=4.5V$	4.4	-	-	V
			$I_O=-4mA$; $V_{CC}=3.0V$	2.48	-	-	V
			$I_O=-8mA$; $V_{CC}=4.5V$	3.8	-	-	V
LOW-level output voltage	V_{OL}	$V_I=V_{IH}$ or V_{IL}	$I_O=50\mu A$; $V_{CC}=2.0V$	-	-	0.1	V
			$I_O=50\mu A$; $V_{CC}=3.0V$	-	-	0.1	V
			$I_O=50\mu A$; $V_{CC}=4.5V$	-	-	0.1	V
			$I_O=4mA$; $V_{CC}=3.0V$	-	-	0.44	V
			$I_O=8mA$; $V_{CC}=4.5V$	-	-	0.44	V
OFF-state output current	I_{OZ}	$V_I=V_{CC}$ or GND; $V_{CC}=5.5V$	-	-	2.5	μA	
input leakage current	I_I	$V_I=5.5V$ or GND; $V_{CC}=0V$ to $5.5V$	-	-	1.0	μA	
supply current	I_{CC}	$V_I=V_{CC}$ or GND; $I_O=0A$; $V_{CC}=5.5V$	-	-	10	μA	
Input capacitance	C_I	-	-	-	10	pF	
AiP74AHCT1G125							
HIGH-level input voltage	V_{IH}	$V_{CC}=4.5V$ to $5.5V$	2.0	-	-	V	
LOW-level input voltage	V_{IL}	$V_{CC}=4.5V$ to $5.5V$	-	-	0.8	V	
HIGH-level output voltage	V_{OH}	$V_I=V_{IH}$ or V_{IL}	$I_O=-50\mu A$; $V_{CC}=4.5V$	4.4	-	-	V
			$I_O=-8mA$; $V_{CC}=4.5V$	3.8	-	-	V
LOW-level output voltage	V_{OL}	$V_I=V_{IH}$ or V_{IL}	$I_O=50\mu A$; $V_{CC}=4.5V$	-	-	0.1	V
			$I_O=8mA$; $V_{CC}=4.5V$	-	-	0.44	V
OFF-state output current	I_{OZ}	$V_I=V_{CC}$ or GND; $V_{CC}=5.5V$	-	-	2.5	μA	



input leakage current	I_I	$V_I=5.5V$ or GND; $V_{CC}=0V$ to $5.5V$	-	-	1.0	μA
supply current	I_{CC}	$V_I=V_{CC}$ or GND; $I_O=0A$; $V_{CC}=5.5V$	-	-	10	μA
additional supply current	ΔI_{CC}	per input pin; $V_I=3.4V$; other inputs at V_{CC} or GND; $I_O=0A$; $V_{CC}=5.5V$	-	-	1.5	mA
input capacitance	C_I	-	-	-	10	pF

3.3.3、DC Characteristics 3

($T_{amb}=-40^{\circ}C$ to $+125^{\circ}C$, voltages are referenced to GND (ground=0V), unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
AiP74AHC1G125							
HIGH-level input voltage	V_{IH}	$V_{CC}=2.0V$	1.5	-	-	V	
		$V_{CC}=3.0V$	2.1	-	-	V	
		$V_{CC}=5.5V$	3.85	-	-	V	
LOW-level input voltage	V_{IL}	$V_{CC}=2.0V$	-	-	0.5	V	
		$V_{CC}=3.0V$	-	-	0.9	V	
		$V_{CC}=5.5V$	-	-	1.65	V	
HIGH-level output voltage	V_{OH}	$V_I=V_{IH}$ or V_{IL}	$I_O=-50\mu A$; $V_{CC}=2.0V$	1.9	-	-	V
			$I_O=-50\mu A$; $V_{CC}=3.0V$	2.9	-	-	V
			$I_O=-50\mu A$; $V_{CC}=4.5V$	4.4	-	-	V
			$I_O=-4mA$; $V_{CC}=3.0V$	2.4	-	-	V
			$I_O=-8mA$; $V_{CC}=4.5V$	3.7	-	-	V
LOW-level output voltage	V_{OL}	$V_I=V_{IH}$ or V_{IL}	$I_O=50\mu A$; $V_{CC}=2.0V$	-	-	0.1	V
			$I_O=50\mu A$; $V_{CC}=3.0V$	-	-	0.1	V
			$I_O=50\mu A$; $V_{CC}=4.5V$	-	-	0.1	V
			$I_O=4mA$; $V_{CC}=3.0V$	-	-	0.55	V
			$I_O=8mA$; $V_{CC}=4.5V$	-	-	0.55	V
OFF-state output current	I_{OZ}	$V_I=V_{CC}$ or GND; $V_{CC}=5.5V$	-	-	10	μA	
input leakage current	I_I	$V_I=5.5V$ or GND; $V_{CC}=0V$ to $5.5V$	-	-	2.0	μA	
supply current	I_{CC}	$V_I=V_{CC}$ or GND; $I_O=0A$; $V_{CC}=5.5V$	-	-	40	μA	
Input capacitance	C_I	-	-	-	10	pF	
AiP74AHCT1G125							
HIGH-level input voltage	V_{IH}	$V_{CC}=4.5V$ to $5.5V$	2.0	-	-	V	
LOW-level input voltage	V_{IL}	$V_{CC}=4.5V$ to $5.5V$	-	-	0.8	V	
HIGH-level output voltage	V_{OH}	$V_I=V_{IH}$ or V_{IL}	$I_O=-50\mu A$; $V_{CC}=4.5V$	4.4	-	-	V
			$I_O=-8mA$; $V_{CC}=4.5V$	3.7	-	-	V



LOW-level output voltage	V_{OL}	$V_I=V_{IH}$ or V_{IL}	$I_O=50\mu A$; $V_{CC}=4.5V$	-	-	0.1	V
			$I_O=8mA$; $V_{CC}=4.5V$	-	-	0.55	V
OFF-state output current	I_{OZ}	$V_I=V_{CC}$ or GND; $V_{CC}=5.5V$		-	-	10	μA
input leakage current	I_I	$V_I=5.5V$ or GND; $V_{CC}=0V$ to $5.5V$		-	-	2.0	μA
supply current	I_{CC}	$V_I=V_{CC}$ or GND; $I_O=0A$; $V_{CC}=5.5V$		-	-	40	μA
additional supply current	ΔI_{CC}	per input pin; $V_I=3.4V$; other inputs at V_{CC} or GND; $I_O=0A$; $V_{CC}=5.5V$		-	-	1.5	mA
input capacitance	C_I	-		-	-	10	pF

3.3.4、AC Characteristics 1

($T_{amb}=25^\circ C$, GND=0V, unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
AiP74AHC1G125							
propagation delay	t_{pd}	A to Y; see Figure 6 ^[1]	$V_{CC}=3.0V$ to $3.6V$ ^[2]				
			$C_L=15pF$	-	4.7	8.0	ns
			$C_L=50pF$	-	6.6	11.5	ns
			$V_{CC}=4.5V$ to $5.5V$ ^[3]				
			$C_L=15pF$	-	3.4	5.5	ns
enable time	t_{en}	\overline{OE} to Y; see Figure 7 ^[1]	$V_{CC}=3.0V$ to $3.6V$ ^[2]				
			$C_L=15pF$	-	5.0	8.0	ns
			$C_L=50pF$	-	6.9	11.5	ns
			$V_{CC}=4.5V$ to $5.5V$ ^[3]				
			$C_L=15pF$	-	3.6	5.1	ns
disable time	t_{dis}	\overline{OE} to Y; see Figure 7 ^[1]	$V_{CC}=3.0V$ to $3.6V$ ^[2]				
			$C_L=15pF$	-	6.0	9.7	ns
			$C_L=50pF$	-	8.3	13.2	ns
			$V_{CC}=4.5V$ to $5.5V$ ^[3]				
			$C_L=15pF$	-	4.1	6.8	ns
Power dissipation capacitance	C_{PD}	per buffer; $C_L=50pF$; $f=1MHz$; $V_I=GND$ to V_{CC} ^[4]		-	9	-	pF
		AiP74AHCT1G125					
propagation delay	t_{pd}	A to Y; see Figure 6 ^[1]	$V_{CC}=4.5V$ to $5.5V$ ^[3]				
			$C_L=15pF$	-	3.4	5.5	ns
			$C_L=50pF$	-	4.8	7.5	ns
enable time	t_{en}	\overline{OE} to Y; see Figure 7 ^[1]	$V_{CC}=4.5V$ to $5.5V$ ^[3]				
			$C_L=15pF$	-	3.9	5.1	ns
			$C_L=50pF$	-	5.1	7.5	ns



disable time	t_{dis}	\overline{OE} to Y; see Figure 7 ^[1]	$V_{CC}=4.5V$ to $5.5V$ ^[3]				
			$C_L=15pF$	-	4.5	6.8	ns
			$C_L=50pF$	-	6.1	8.8	ns
power dissipation capacitance	C_{PD}	per buffer; $C_L=50pF$; $f=1MHz$; $V_I=GND$ to V_{CC} ^[4]	-	11	-	pF	

Note:

[1] t_{pd} is the same as t_{PLH} and t_{PHL} . t_{en} is the same as t_{PZL} and t_{PZH} . t_{dis} is the same as t_{PLZ} and t_{PHZ} .[2] Typical values are measured at $V_{CC}=3.3V$.[3] Typical values are measured at $V_{CC}=5V$.[4] C_{PD} is used to determine the dynamic power dissipation (P_D in uW). $P_D=C_{PD} \times V_{CC}^2 \times f_i + \sum(C_L \times V_{CC}^2 \times f_o)$ where: f_i =input frequency in MHz; f_o =output frequency in MHz; C_L =output load capacitance in pF; V_{CC} =supply voltage in Volts.

3.3.5、AC Characteristics 2

(T_{amb}=-40°C to +85°C, GND=0V, unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
AiP74AHC1G125							
propagation delay	t_{pd}	A to Y; see Figure 6 ^[1]	$V_{CC}=3.0V$ to $3.6V$ ^[2]				
			$C_L=15pF$	1.0	-	9.5	ns
			$C_L=50pF$	1.0	-	13.0	ns
			$V_{CC}=4.5V$ to $5.5V$ ^[3]				
			$C_L=15pF$	1.0	-	6.5	ns
			$C_L=50pF$	1.0	-	8.5	ns
enable time	t_{en}	\overline{OE} to Y; see Figure 7 ^[1]	$V_{CC}=3.0V$ to $3.6V$ ^[2]				
			$C_L=15pF$	1.0	-	9.5	ns
			$C_L=50pF$	1.0	-	13.0	ns
			$V_{CC}=4.5V$ to $5.5V$ ^[3]				
			$C_L=15pF$	1.0	-	6.0	ns
			$C_L=50pF$	1.0	-	8.5	ns
disable time	t_{dis}	\overline{OE} to Y; see Figure 7 ^[1]	$V_{CC}=3.0V$ to $3.6V$ ^[2]				
			$C_L=15pF$	1.0	-	11.5	ns
			$C_L=50pF$	1.0	-	15.0	ns
			$V_{CC}=4.5V$ to $5.5V$ ^[3]				
			$C_L=15pF$	1.0	-	8.0	ns
			$C_L=50pF$	1.0	-	10.0	ns
Power dissipation capacitance	C_{PD}	per buffer; $C_L=50pF$; $f=1MHz$; $V_I=GND$ to V_{CC} ^[4]	-	-	-	pF	
AiP74AHCT1G125							
propagation delay	t_{pd}	A to Y; see Figure 6 ^[1]	$V_{CC}=4.5V$ to $5.5V$ ^[3]				
			$C_L=15pF$	1.0	-	6.5	ns



			$C_L=50\text{pF}$	1.0	-	8.5	ns
enable time	t_{en}	$\overline{\text{OE}}$ to Y; see Figure 7 ^[1]	$V_{\text{CC}}=4.5\text{V to }5.5\text{V}^{[3]}$				
			$C_L=15\text{pF}$	1.0	-	6.0	ns
			$C_L=50\text{pF}$	1.0	-	8.5	ns
disable time	t_{dis}	$\overline{\text{OE}}$ to Y; see Figure 7 ^[1]	$V_{\text{CC}}=4.5\text{V to }5.5\text{V}^{[3]}$				
			$C_L=15\text{pF}$	1.0	-	8.0	ns
			$C_L=50\text{pF}$	1.0	-	10.0	ns
power dissipation capacitance	C_{PD}	per buffer; $C_L=50\text{pF}$; $f=1\text{MHz}$; $V_I=\text{GND to }V_{\text{CC}}^{[4]}$		-	-	-	pF

Note:

[1] t_{pd} is the same as t_{PLH} and t_{PHL} . t_{en} is the same as t_{PZL} and t_{PZH} . t_{dis} is the same as t_{PLZ} and t_{PHZ} .[2] Typical values are measured at $V_{\text{CC}}=3.3\text{V}$.[3] Typical values are measured at $V_{\text{CC}}=5\text{V}$.[4] C_{PD} is used to determine the dynamic power dissipation (P_D in uW). $P_D=C_{\text{PD}}\times V_{\text{CC}}^2\times f_i+\sum(C_L\times V_{\text{CC}}^2\times f_o)$ where: f_i =input frequency in MHz; f_o =output frequency in MHz; C_L =output load capacitance in pF; V_{CC} =supply voltage in Volts.

3.3.6、AC Characteristics 3

(T_{amb}=-40°C to +125°C, GND=0V, unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
AiP74AHC1G125							
propagation delay	t_{pd}	A to Y; see Figure 6 ^[1]	$V_{\text{CC}}=3.0\text{V to }3.6\text{V}^{[2]}$				
			$C_L=15\text{pF}$	1.0	-	11.5	ns
			$C_L=50\text{pF}$	1.0	-	14.5	ns
			$V_{\text{CC}}=4.5\text{V to }5.5\text{V}^{[3]}$				
			$C_L=50\text{pF}$	1.0	-	9.5	ns
enable time	t_{en}	$\overline{\text{OE}}$ to Y; see Figure 7 ^[1]	$V_{\text{CC}}=3.0\text{V to }3.6\text{V}^{[2]}$				
			$C_L=15\text{pF}$	1.0	-	11.5	ns
			$C_L=50\text{pF}$	1.0	-	14.5	ns
			$V_{\text{CC}}=4.5\text{V to }5.5\text{V}^{[3]}$				
			$C_L=50\text{pF}$	1.0	-	9.5	ns
disable time	t_{dis}	$\overline{\text{OE}}$ to Y; see Figure 7 ^[1]	$V_{\text{CC}}=3.0\text{V to }3.6\text{V}^{[2]}$				
			$C_L=15\text{pF}$	1.0	-	12.5	ns
			$C_L=50\text{pF}$	1.0	-	16.5	ns
			$V_{\text{CC}}=4.5\text{V to }5.5\text{V}^{[3]}$				
			$C_L=50\text{pF}$	1.0	-	11.0	ns



Power dissipation capacitance	C_{PD}	per buffer; $C_L=50\text{pF}$; $f=1\text{MHz}$; $V_I=\text{GND to } V_{CC}^{[4]}$	-	-	-	pF	
AiP74AHCT1G125							
propagation delay	t_{pd}	A to Y; see Figure 6 ^[1]	$V_{CC}=4.5\text{V to } 5.5\text{V}^{[3]}$				
			$C_L=15\text{pF}$	1.0	-	7.0	ns
			$C_L=50\text{pF}$	1.0	-	9.5	ns
enable time	t_{en}	$\overline{\text{OE}}$ to Y; see Figure 7 ^[1]	$V_{CC}=4.5\text{V to } 5.5\text{V}^{[3]}$				
			$C_L=15\text{pF}$	1.0	-	6.5	ns
			$C_L=50\text{pF}$	1.0	-	9.5	ns
disable time	t_{dis}	$\overline{\text{OE}}$ to Y; see Figure 7 ^[1]	$V_{CC}=4.5\text{V to } 5.5\text{V}^{[3]}$				
			$C_L=15\text{pF}$	1.0	-	8.5	ns
			$C_L=50\text{pF}$	1.0	-	11.0	ns
power dissipation capacitance	C_{PD}	per buffer; $C_L=50\text{pF}$; $f=1\text{MHz}$; $V_I=\text{GND to } V_{CC}^{[4]}$	-	-	-	pF	

Note:

[1] t_{pd} is the same as t_{PLH} and t_{PHL} . t_{en} is the same as t_{PZL} and t_{PZH} . t_{dis} is the same as t_{PLZ} and t_{PHZ} .[2] Typical values are measured at $V_{CC}=3.3\text{V}$.[3] Typical values are measured at $V_{CC}=5\text{V}$.[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW). $P_D=C_{PD}\times V_{CC}^2\times f_i+\sum(C_L\times V_{CC}^2\times f_o)$ where: f_i =input frequency in MHz; f_o =output frequency in MHz; C_L =output load capacitance in pF; V_{CC} =supply voltage in Volts.



4、Testing Circuit

4.1、AC Testing Circuit

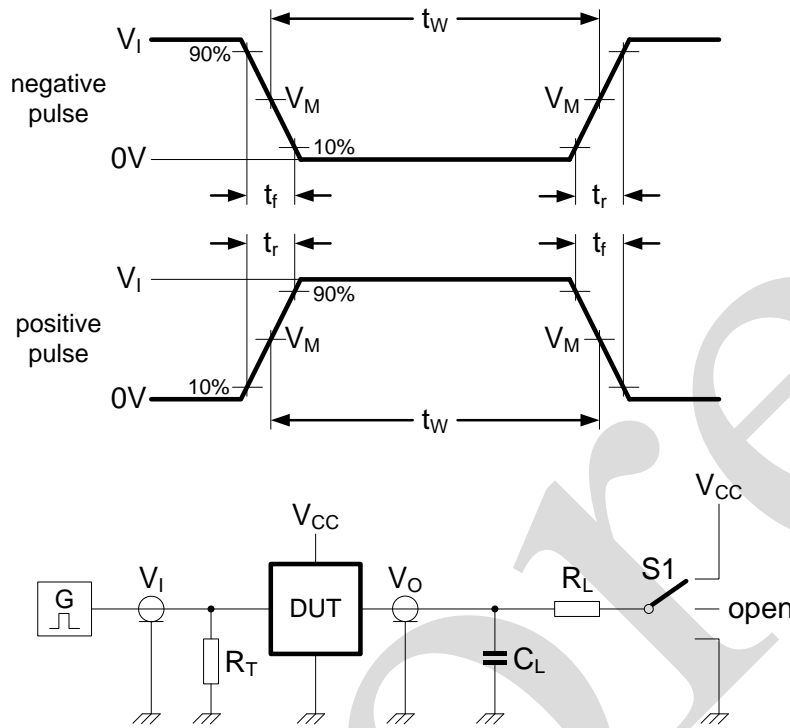


Figure 5. Test circuit for measuring switching times

Definitions test circuit:

R_T =Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L =Load capacitance including jig and probe capacitance.

R_L =Load resistance.

S1=Test selection switch.

4.2、AC Testing Waveforms

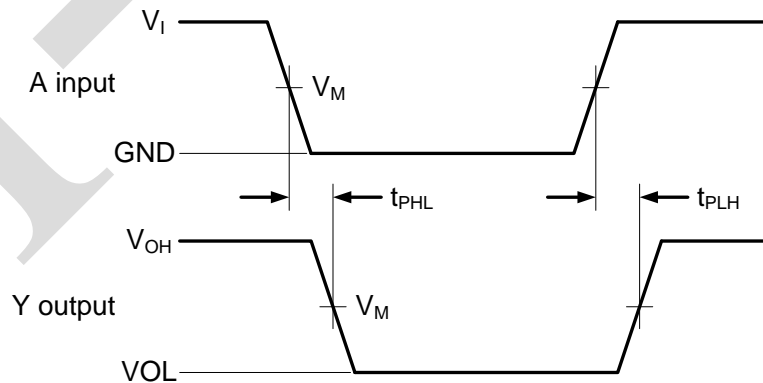


Figure 6. Input (A) to output (Y) propagation delays

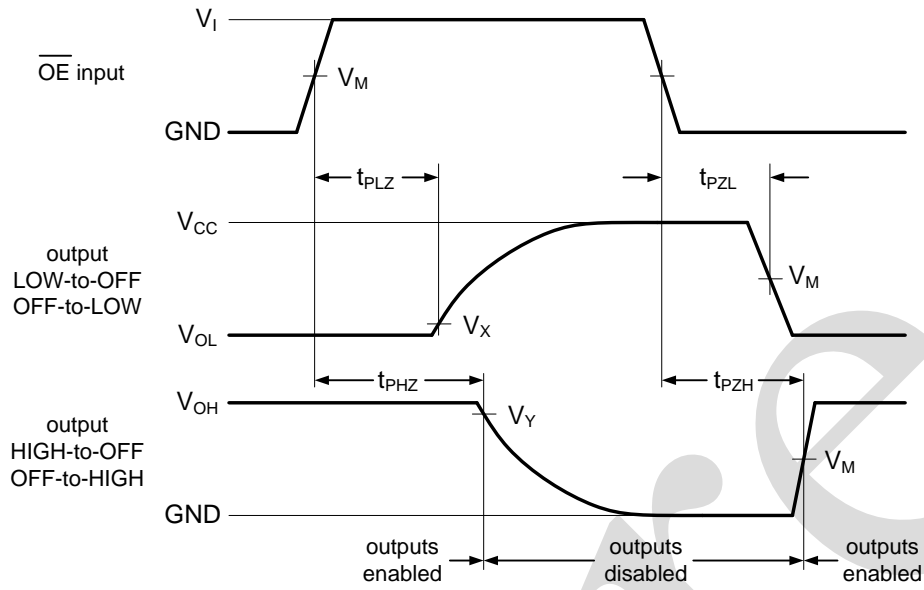


Figure 7. Enable and disable times

4.3. Measurement Points

Type	Inputs		Outputs		
	V_I	V_M	V_M	V_X	V_Y
AiP74AHC1G125	GND to V_{CC}	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.3V$	$V_{OH} - 0.3V$
AiP74AHCT1G125	GND to 3.0V	1.5V	$0.5 \times V_{CC}$	$V_{OL} + 0.3V$	$V_{OH} - 0.3V$

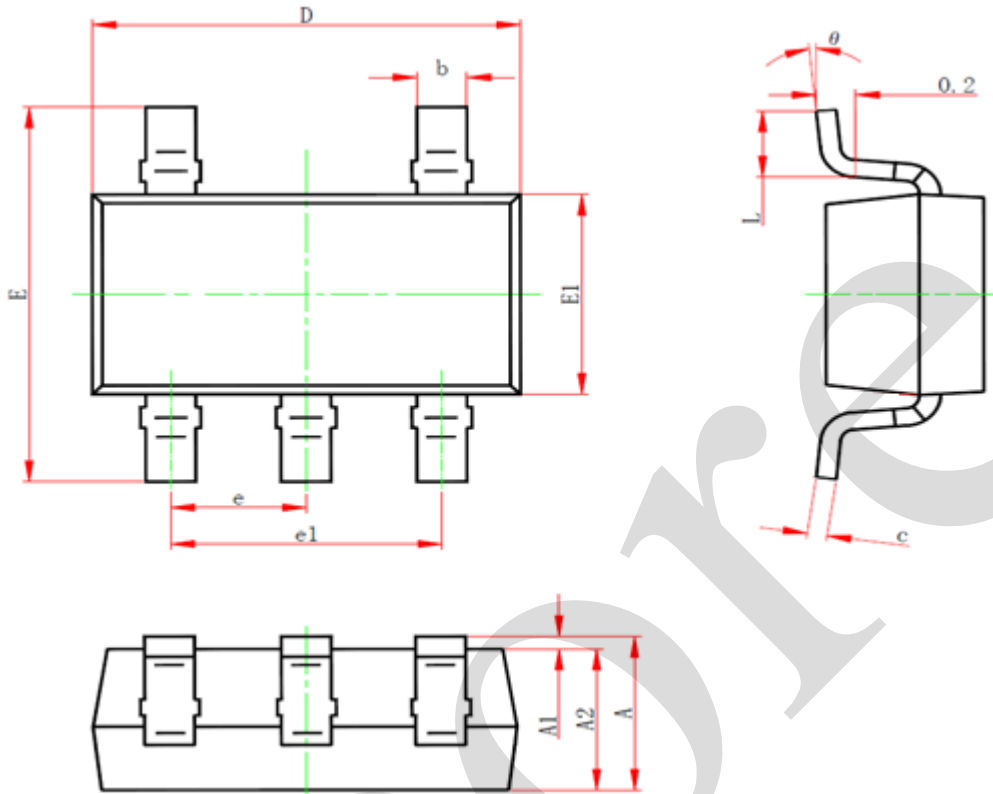
4.4. Test Data

Type	Inputs		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
AiP74AHC1G125	V_{CC}	$\leq 3ns$	15pF, 50pF	1k Ω	open	GND	V_{CC}
AiP74AHCT1G125	3V	$\leq 3ns$	15pF, 50pF	1k Ω	open	GND	V_{CC}



5、Package Information

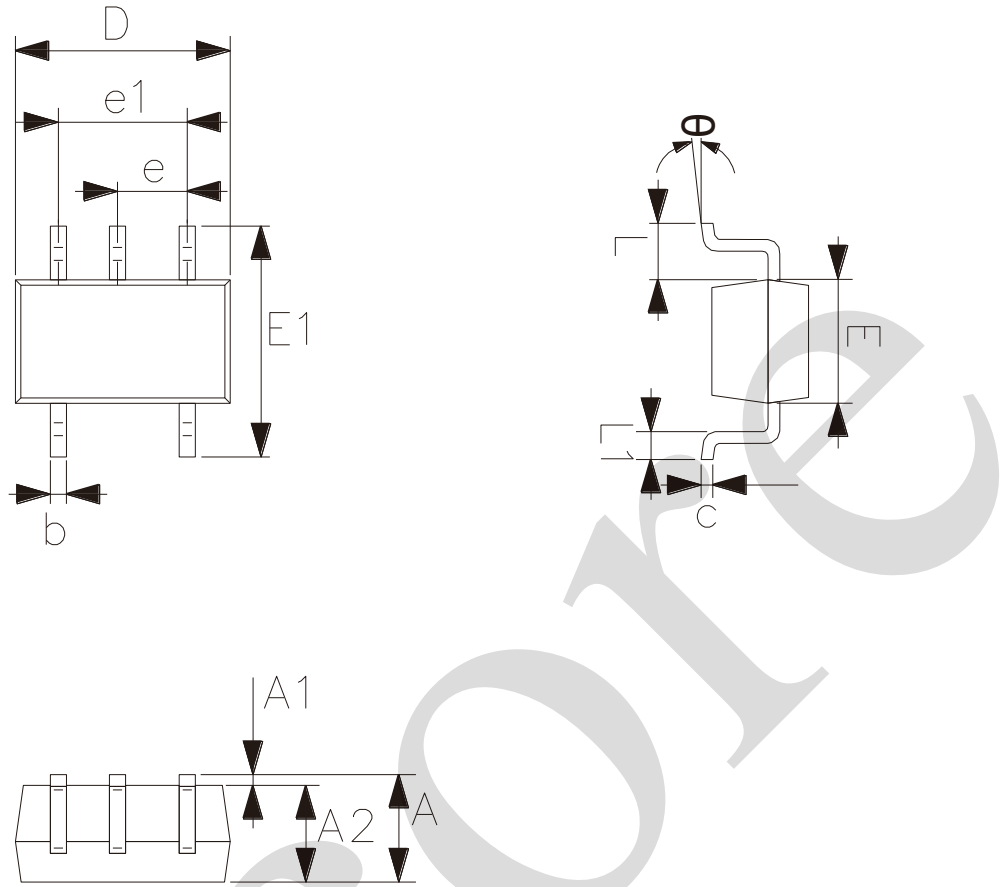
5.1、SOT23-5



Symbol	Dimensions (mm)	
	Min.	Max.
A	-	1.26
A1	0.00	0.12
A2	1.00	1.20
b	0.30	0.50
c	0.10	0.20
D	2.82	3.02
E	2.60	3.00
E1	1.50	1.70
e	0.95	
e1	1.80	2.00
L	0.30	0.60
θ	0°	8°



5.2、SOT353



Symbol	Dimensions (mm)	
	Min.	Max.
A	0.90	1.10
A1	0.00	0.10
A2	0.90	1.00
b	0.15	0.35
c	0.11	0.175
D	2.00	2.20
E	1.15	1.35
E1	2.15	2.45
e	0.65	
e1	1.20	1.40
L	0.525	
L1	0.26	0.46
θ	0°	8°



6、 Statements And Notes

6.1、 The name and content of Hazardous substances or Elements in the product

Part name	Hazardous substances or Elements									
	Lead and lead compounds	Mercury and mercury compounds	Cadmium and cadmium compounds	Hexavalent chromium compounds	Polybrominated biphenyls	Polybrominated biphenyl ethers	Dibutyl phthalate	Butylbenzyl phthalate	Di-2-ethylhexyl phthalate	Diisobutyl phthalate
Lead frame	○	○	○	○	○	○	○	○	○	○
Plastic resin	○	○	○	○	○	○	○	○	○	○
Chip	○	○	○	○	○	○	○	○	○	○
The lead	○	○	○	○	○	○	○	○	○	○
Plastic sheet installed	○	○	○	○	○	○	○	○	○	○
explanation	○: Indicates that the content of hazardous substances or elements in the detection limit of the following the SJ/T11363-2006 standard. ×: Indicates that the content of hazardous substances or elements exceeding the SJ/T11363-2006 Standard limit requirements.									

6.2、 Notes

We Recommend you to read this chapter carefully before using this product.

The information in this chapter is provided for reference only and i-Core disclaims any express or implied warranties, including but not limited to applicability, special application or non-infringement of third party rights.

This product is not suitable for critical equipment such as life-saving, life-sustaining or safety equipment. It is also not suitable for applications that may result in personal injury, death, or serious property or environmental damage due to product malfunction or failure. I-Core will not be liable for any damages incurred by the customers at their own risk for such applications.

The customer is responsible for conducting all necessary tests i-Core's application to avoid failure in the application or the application of the customer's third party users. I-Core does not accept any liability.

The Company reserves the right to change or improve the information published in this chapter at any time. The information in this chapter are subject to change without notice. We recommend the customer to consult our sales staff before purchasing.

Please obtain related materials form i-Core's regular channels and we are not responsible for its content if it is provided by sources other than our company.

In case of any conflict between the Chinese and English version, the version is subject to the Chinese one.